

O Moutanabbir

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

39
papers

738
citations

15
h-index

26
g-index

43
ext. papers

952
ext. citations

7
avg, IF

4.35
L-index

#	Paper	IF	Citations
39	Enhanced GeSn Microdisk Lasers Directly Released on Si. <i>Advanced Optical Materials</i> , 2022 , 10, 2101213	8.1	5
38	Extended-SWIR Photodetection in All-Group IV Core/Shell Nanowires. <i>ACS Photonics</i> , 2022 , 9, 914-921	6.3	1
37	Recrystallization and interdiffusion processes in laser-annealed strain-relaxed metastable Ge _{0.89} Sn _{0.11} . <i>Journal of Applied Physics</i> , 2022 , 131, 105304	2.5	0
36	Ge _{0.92} Sn _{0.08} core-shell single nanowire infrared photodetector with superior characteristics for on-chip optical communication. <i>Applied Physics Letters</i> , 2022 , 120, 171110	3.4	2
35	A Light-Hole Germanium Quantum Well on Silicon.. <i>Advanced Materials</i> , 2022 , e2201192	24	0
34	1D photonic crystal direct bandgap GeSn-on-insulator laser. <i>Applied Physics Letters</i> , 2021 , 119, 201101	3.4	7
33	Atomic Pathways of Solute Segregation in the Vicinity of Nanoscale Defects. <i>Nano Letters</i> , 2021 , 21, 9882-9888	2.9	1
32	Monolithic infrared silicon photonics: The rise of (Si)GeSn semiconductors. <i>Applied Physics Letters</i> , 2021 , 118, 110502	3.4	20
31	Combined Iodine- and Sulfur-Based Treatments for an Effective Passivation of GeSn Surface. <i>Journal of Physical Chemistry C</i> , 2021 , 125, 9516-9525	3.8	3
30	All-Group IV Transferable Membrane Mid-Infrared Photodetectors. <i>Advanced Functional Materials</i> , 2021 , 31, 2006329	15.6	15
29	Midinfrared Emission and Absorption in Strained and Relaxed Direct-Band-Gap Ge _{1-x} Sn _x Semiconductors. <i>Physical Review Applied</i> , 2021 , 15,	4.3	6
28	Composition uniformity and large degree of strain relaxation in MBE-grown thick GeSn epitaxial layers, containing 16% Sn. <i>Journal Physics D: Applied Physics</i> , 2021 , 54, 185105	3	6
27	Extended Short-Wave Infrared Absorption in Group-IV Nanowire Arrays. <i>Physical Review Applied</i> , 2021 , 15,	4.3	1
26	Decoupling the effects of composition and strain on the vibrational modes of GeSn semiconductors. <i>Semiconductor Science and Technology</i> , 2020 , 35, 095006	1.8	8
25	Effects of short-range order and interfacial interactions on the electronic structure of two-dimensional antimony-arsenic alloys. <i>Journal of Applied Physics</i> , 2020 , 127, 025305	2.5	1
24	Dislocation Pipe Diffusion and Solute Segregation during the Growth of Metastable GeSn. <i>Crystal Growth and Design</i> , 2020 , 20, 3493-3498	3.5	15
23	2D Antimony-Arsenic Alloys. <i>Small</i> , 2020 , 16, e1906540	11	4

22	3D Atomic Mapping of Interfacial Roughness and Its Spatial Correlation Length in Sub-10 nm Superlattices. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 1728-1736	9.5	3
21	Pnictogens Allotropy and Phase Transformation during van der Waals Growth. <i>Nano Letters</i> , 2020 , 20, 8258-8266	11.5	2
20	Vanishing Zeeman energy in a two-dimensional hole gas. <i>Physical Review B</i> , 2020 , 102,	3.3	4
19	Atomic-Scale Insights into Semiconductor Heterostructures: From Experimental Three-Dimensional Analysis of the Interface to a Generalized Theory of Interfacial Roughness Scattering. <i>Physical Review Applied</i> , 2020 , 13,	4.3	10
18	Dynamics of Antimonene-Graphene Van Der Waals Growth. <i>Advanced Materials</i> , 2019 , 31, e1900569	24	23
17	Vacancy complexes in nonequilibrium germanium-tin semiconductors. <i>Applied Physics Letters</i> , 2019 , 114, 251907	3.4	19
16	Enhanced Sn incorporation in GeSn epitaxial semiconductors via strain relaxation. <i>Journal of Applied Physics</i> , 2019 , 125, 025304	2.5	44
15	Effect of Hydrogen Implantation on the Mechanical Properties of AlN throughout Ion-Induced Splitting. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, P180-P184	2	
14	Reduction of Thermal Conductivity in Nanowires by Combined Engineering of Crystal Phase and Isotope Disorder. <i>Nano Letters</i> , 2018 , 18, 3066-3075	11.5	7
13	Recovering the Semiconductor Properties of the Epitaxial Group V 2D Materials Antimonene and Arsenene. <i>Journal of Physical Chemistry C</i> , 2018 , 122, 9162-9168	3.8	18
12	Extreme IR absorption in group IV-SiGeSn core-shell nanowires. <i>Journal of Applied Physics</i> , 2018 , 123, 223102	2.5	5
11	Atomically uniform Sn-rich GeSn semiconductors with 3.0B.5 μ m room-temperature optical emission. <i>Applied Physics Letters</i> , 2018 , 112, 251903	3.4	45
10	Short-range atomic ordering in nonequilibrium silicon-germanium-tin semiconductors. <i>Physical Review B</i> , 2017 , 95,	3.3	13
9	Synthesis of Antimonene on Germanium. <i>Nano Letters</i> , 2017 , 17, 4970-4975	11.5	157
8	Phonon Engineering in Isotopically Disordered Silicon Nanowires. <i>Nano Letters</i> , 2015 , 15, 3885-93	11.5	27
7	Thermal transport through short-period SiGe nanodot superlattices. <i>Journal of Applied Physics</i> , 2014 , 115, 044312	2.5	20
6	Preparation of nanowire specimens for laser-assisted atom probe tomography. <i>Nanotechnology</i> , 2014 , 25, 435704	3.4	13
5	Colossal injection of catalyst atoms into silicon nanowires. <i>Nature</i> , 2013 , 496, 78-82	50.4	130

4	Strain and composition effects on Raman vibrational modes of silicon-germanium-tin ternary alloys. <i>Applied Physics Letters</i> , 2013 , 103, 263103	3-4	51
3	Fast atom beam-activated n-Si/n-GaAs wafer bonding with high interfacial transparency and electrical conductivity. <i>Journal of Applied Physics</i> , 2013 , 113, 203512	2-5	29
2	Dynamic probe of atom exchange during monolayer growth. <i>Physical Review B</i> , 2012 , 85,	3-3	2
1	Experimental elucidation of vacancy complexes associated with hydrogen ion-induced splitting of bulk GaN. <i>Physical Review B</i> , 2010 , 81,	3-3	16